

## EAST Search History

## EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	62570	((apply\$3 or bias) near2 (voltage)) with (alter\$3 or conver\$5 or chang\$3 or insulat\$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/10/29 11:01
L2	1144	(TANAKA near2 KOICHIRO ). inv.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/10/29 11:01
L3	239	(ISOBE near2 ATSUO ).inv.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/10/29 11:01
L4	914	(YAMAMOTO near2 YOSHI AKI ).inv.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/10/29 11:01
L5	15	(L2 or L3 or L4 ) and L1	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/10/29 11:01
L6	3	"20060270073"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/10/29 11:23

L7	19	("20010009222"   "20010019129"   "20010020987"   "20040072411"   "20040101989"   "20050017239"   "20050037549"   "20050152658"   "20050196883"   "20050253178"   "20050273290"   "20070010057"   "5576556"   "5962897"   "6455875"   "6559010"   "6790749"   "6887724"   "6911358").PN. OR ("7550382").URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/10/29 11:23
L8	0	"5576556" "5962897" "6455875" "6559010" "6790749" "6887724" "6911358" 2001/0009222 2001/0019129 2001/0020987 2004/0072411 2004/0101989 2005/0017239 2005/0037549 2005/0152658 2005/0196883 2005/0253178 November "2005" Yamaguchi et "al." 257/301 2005/0273290 December "2005" Asano et "al." 702/117 2007/0010057	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/10/29 11:24
L9	179	"5576556" "5962897" "6455875" "6559010" "6790749" "6887724" "6911358" "20010009222" "20010019129" "20010020987" "20040072411" "20040101989" "20050017239" "20050037549" "20050152658" "20050196883" "20050253178" "20050273290" "20070010057"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/10/29 11:26
L10	151	9 and (VOLTAGE OR APPLY \$3 OR BIAS\$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/10/29 11:26
L11	147	10 AND (SEMICONDUCTOR)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/10/29 11:27

L12	701889	((fuse or (anti\$1fuse)) or WOM or (write near2 once) or (IC tage) or (RF tag) ) and ((thin film transistor) or (TFT or (thinfilm transistor)))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/10/29 12:41
L13	4467	((apply\$3 or bias) near2 (voltage)) with (alter\$3 or conver\$5 or chang\$3 or insulat\$3) with (semiconductor or semi \$1conductor or (amorphous) or crystalline)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/10/29 12:42
L14	1081	12 and 13	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/10/29 12:42
L15	76	((((fuse or (anti\$1fuse)) or WOM or (write near2 once) or (IC tage) or (RF tag) ) and ((thin film transistor) or (TFT or (thinfilm transistor)))) same (((apply\$3 or bias) near2 (voltage)) with (alter \$3 or conver\$5 or chang\$3 or insulat\$3) with (semiconductor or semi \$1conductor or (amorphous) or crystalline))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/10/29 12:43
L21	12	((first and second) (memory cell) ) same ((thinfilm transistor) or (thin film transistor) or TFT)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/10/29 14:44
L22	1	("20020126108").pn. and ((semiconductor film) or (island))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/10/29 15:22
L23	67	(257/16).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/10/29 15:55
L24	330	(257/49).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/10/29 15:55
L25	336	(257/52).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/10/29 15:55
L26	3423	(257/59).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/10/29 15:55
L27	422	(257/64).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/10/29 15:55

L28	278	(257/68).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/10/29 15:55
L29	1240	(257/770-772).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/10/29 15:55
L30	368	(438/153).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/10/29 15:56
L31	1579	(438/166).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/10/29 15:56
L32	2890	(438/238-239).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/10/29 15:56
L33	1211	(438/478).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/10/29 15:56
S1	1	"20050174845"	DERWENT	ADJ	ON	2009/10/28 12:30
S3	1	10/573527	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/10/28 12:32
S7	2	JP "2004030681"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/10/28 12:59
S8	1918	(Jun near2 Koyama).inv.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/10/28 13:01
S9	651	(semiconductor).ti. and S8	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/10/28 13:02
S10	197	chip and S9	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/10/28 13:02
S11	772	(KATO near2 KIYOSHI).inv.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/10/28 13:17

S12	145	(impurity region) and S11	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/10/28 13:17
S13	135	voltage and S12	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/10/28 13:17
S14	134	gate and S13	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/10/28 13:18
S15	134	memory and S14	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/10/28 13:18
S16	34	(short circuit\$3) and S15	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/10/28 13:21
S17	772	((KATO near2 KIYOSHI).inv.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/10/28 15:19
S18	52	((((short circuit\$3) or (burn\$3 or alter\$3 or chang\$3)) with (channel or dielectric or insulat\$3)) and S17	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/10/28 15:19
S19	23	((((short circuit\$3) or (burn\$3 or alter\$3 or chang\$3)) with (channel or dielectric or insulat\$3) with (voltage or bias or current)) and S17	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/10/28 15:31
S20	1	WO "1996007300"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/10/28 15:58

S21	21	"5798534"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/10/28 15:58
S22	38860	(alter\$3 or chang\$3 or conver\$4) with (semiconductor or (amorphous silicon) or (a \$1Si) or (SiGe) or (amorphous Si)) with (voltage or current or bias)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/10/28 16:12
S23	1708	((thin film transistor) or (thinfilm transistor)) and S22	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/10/28 16:13
S24	1681	S23 and (memory or source or drain or gate or dielectric or insula\$5)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/10/28 16:13
S25	204	((insulat\$5 or (non\$1conduct \$3)) near2 (state or mode)) and S24	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/10/28 17:31
S27	24180	(( (IC tag) or (write once memory) or WOM)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/10/29 10:43
S28	62570	((apply\$3 or bias) near2 (voltage)) with (alter\$3 or conver\$5 or chang\$3 or insulat\$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/10/29 10:44
S29	4	S27 same S28	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/10/29 10:44
S30	1	"20090173893"	DERWENT	ADJ	ON	2009/10/29 10:50

S31	2	WO "2006022196"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/10/29 10:52
S32	1144	(TANAKA near2 KOICHIRO ). inv.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/10/29 10:58
S33	239	(ISOBE near2 ATSUO ).inv.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/10/29 10:59
S34	914	(YAMAMOTO near2 YOSHI AKI ).inv.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/10/29 10:59

**EAST Search History (I nterference)**

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